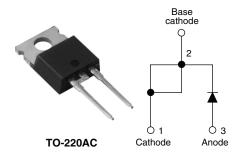




Vishay High Power Products

## Input Rectifier Diode, 20 A



PRODUCT SUMMARY			
V <sub>F</sub> at 10 A < 1 V			
I <sub>FSM</sub>	300 A		
$V_{RRM}$	800/1200 V		

#### **DESCRIPTION/FEATURES**

The 20ETS.. rectifier High Voltage Series has been optimized for very low forward voltage drop, with moderate leakage. The glass passivation technology used has reliable operation up to 150 °C junction temperature.

Typical applications are in input rectification and these products are designed to be used with Vishay HPP switches and output rectifiers which are available in identical package outlines.

This product series has been designed and qualified for industrial level.

OUTPUT CURRENT IN TYPICAL APPLICATIONS			
APPLICATIONS	SINGLE-PHASE BRIDGE	THREE-PHASE BRIDGE	UNITS
Capacitive input filter T <sub>A</sub> = 55 °C, T <sub>J</sub> = 125 °C common heatsink of 1 °C/W	16.3	21	А

MAJOR RATINGS AND CHARACTERISTICS				
SYMBOL	CHARACTERISTICS	VALUES	UNITS	
I <sub>F(AV)</sub>	Sinusoidal waveform	20	А	
$V_{RRM}$		800/1200	V	
I <sub>FSM</sub>		300	Α	
V <sub>F</sub>	10 A, T <sub>J</sub> = 25 °C	1.0	V	
TJ		- 40 to 150	°C	

VOLTAGE RATINGS				
PART NUMBER	V <sub>RRM</sub> , MAXIMUM PEAK REVERSE VOLTAGE V	V <sub>RSM</sub> , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	I <sub>RRM</sub> AT 150 °C mA	
20ETS08	800	900	1	
20ETS12	1200	1300	1	

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum average forward current	I <sub>F(AV)</sub>	T <sub>C</sub> = 105 °C, 180° conduction half sine wave	20	
Maximum peak one cycle		10 ms sine pulse, rated V <sub>RRM</sub> applied	250	Α
non-repetitive surge current	IFSM	10 ms sine pulse, no voltage reapplied	300	
Maximum I <sup>2</sup> t for fusing	l <sup>2</sup> t	10 ms sine pulse, rated V <sub>RRM</sub> applied	316	A <sup>2</sup> s
Maximum 1-t for fusing	1-1	10 ms sine pulse, no voltage reapplied	442	A-S
Maximum I <sup>2</sup> √t for fusing	I <sup>2</sup> √t	t = 0.1 ms to 10 ms, no voltage reapplied	4420	A²√s

# 20ETS.. High Voltage Series

## Vishay High Power Products Input Rectifier Diode, 20 A



ELECTRICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum forward voltage drop	V <sub>FM</sub>	20 A, T <sub>J</sub> = 25 °C		1.1	V
Forward slope resistance	r <sub>t</sub>	T 150 °C		10.4	mΩ
Threshold voltage	V <sub>F(TO)</sub>	T <sub>J</sub> = 150 °C 0.85		V	
Maximum reverse leakage current		T <sub>J</sub> = 25 °C	$V_{B}$ = Rated $V_{BBM}$	0.1	mA
iviaximum reverse leakage current	I <sub>RM</sub>	T <sub>J</sub> = 150 °C	VR = nateu VRRM	1.0	IIIA

THERMAL - MECHA	THERMAL - MECHANICAL SPECIFICATIONS				
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction and stora temperature range	ge	T <sub>J</sub> , T <sub>Stg</sub>		- 40 to 150	°C
Maximum thermal resistance junction to case	€,	$R_{thJC}$	DC operation	1.3	°C/W
Typical thermal resistance, case to heatsink  R <sub>thCS</sub> Mounting surface, smooth an		Mounting surface, smooth and greased	0.5	C/VV	
Approximate weight				2	g
Approximate weight				0.07	OZ.
Mauration to minim				6 (5)	kgf · cm
Mounting torque maxim	maximum			12 (10)	(lbf $\cdot$ in)
Marking device			Consisted TO 000AC	20E	TS08
			Case style TO-220AC	20ETS12	



## Input Rectifier Diode, 20 A Vishay High Power Products

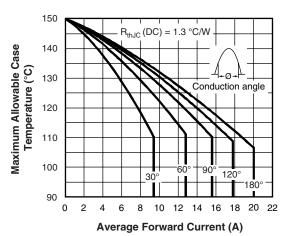


Fig. 1 - Current Rating Characteristics

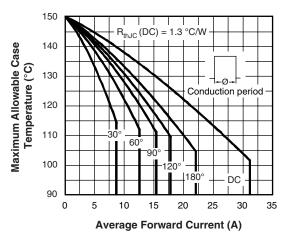


Fig. 2 - Current Rating Characteristics

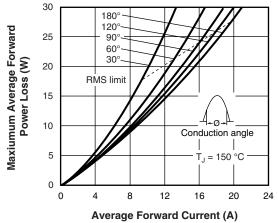


Fig. 3 - Forward Power Loss Characteristics

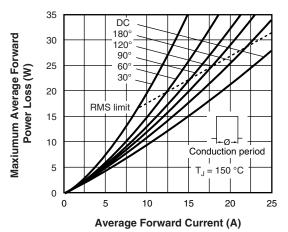
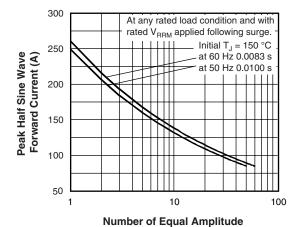


Fig. 4 - Forward Power Loss Characteristics



Half Cycle Current Pulse (N)
Fig. 5 - Maximum Non-Repetitive Surge Current

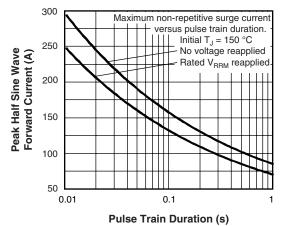


Fig. 6 - Maximum Non-Repetitive Surge Current

## Vishay High Power Products Input Rectifier Diode, 20 A



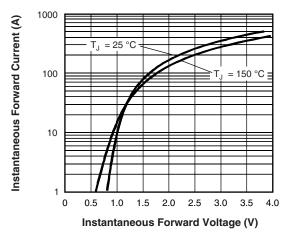


Fig. 7 - Forward Voltage Drop Characteristics

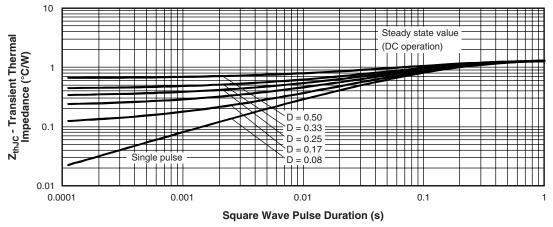


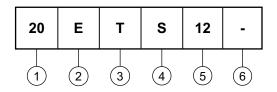
Fig. 8 - Thermal Impedance  $Z_{thJC}$  Characteristics



Input Rectifier Diode, 20 A Vishay High Power Products

#### **ORDERING INFORMATION TABLE**

**Device code** 



1 - Current rating (20 = 20 A)

2 - Circuit configuration:

E = Single diode

- Package:

T = TO-220

4 - Type of silicon:

S = Standard recovery rectifier

5 - Voltage code x 100 = V<sub>RRM</sub> - 0

08 = 800 V 12 = 1200 V

6 - • None = Standard production

• PbF = Lead (Pb)-free

LINKS TO RELATED DOCUMENTS			
Dimensions <u>www.vishay.com/doc?95221</u>			
Part marking information	www.vishay.com/doc?95224		



Vishay

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